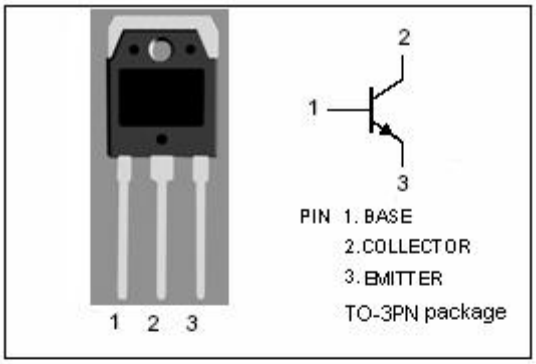
SPTECH Silicon NPN Power Transistor



DESCRIPTION

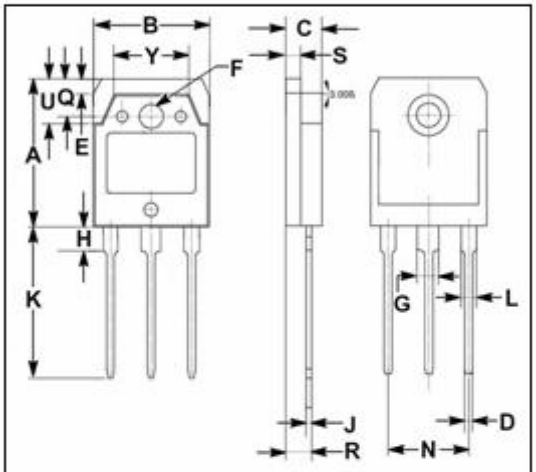
- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$=250V(Min)
- Good Linearity of h_{FE}
- Complement to Type NJW0302G

APPLICATIONS

- Designed for high fidelity audio amplifier and other linear applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	250	V
V_{CEO}	Collector-Emitter Voltage	250	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	15	A
I_B	Base Current-Continuous	1.5	A
P_C	Collector Power Dissipation @ T_C=25℃	150	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃



DIM	mm MIN	mm MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

SPTECH Silicon NPN Power Transistor

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 30mA ; I_B= 0	250			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5.0A; I_B= 0.5A			1.0	V
$V_{BE(on)}$	Base−Emitter On Voltage	I_C = 5.0 A, V_{CE} = 5.0 V			1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 250V ; I_E= 0			10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			5	μA
h_{FE}	DC Current Gain	I_C= 0.5A ; V_{CE}= 5V	75		150	
h_{FE1}	DC Current Gain	I_C= 1A ; V_{CE}= 5V	75		150	
h_{FE2}	DC Current Gain	I_C= 3A ; V_{CE}= 5V	75		150	
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= 10V;f_{test}= 1.0MHz			700	pF
f_T	Current-Gain—Bandwidth Product	I_C=-1A ; V_{CE}= 5V ;f_{test}= 1.0MHz	20			MHz